



Product Summary

BV _{DSS}	Max R _{DS(on)} MAX	Max I _D MAX T _A = 25°C		
30V	$65m\Omega @ V_{GS} = 10V$	3.2A		
300	$95m\Omega @ V_{GS} = 4.5V$	2.6A		

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

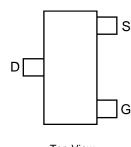
- Low on-resistance
- Fast switching speed
- Low gate charge
- Low threshold
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

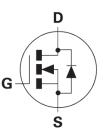
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish —Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



Top View



Top View Pin Out



Equivalent Circuit

Ordering Information (Note 5)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN3A14FQTA	314	7	8	3,000 Units

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.htmlfor more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units	
Drain-Source Voltage				V _{DSS}	30	V
Gate-Source Voltage			V _{GS}	±20	V	
Continuous Drain Current	V _{GS} = 10V	$T_A = 70^{\circ}C$	(Note 7) (Note 7) (Note 6)	ID	3.9 3.2 3.2	A
Pulsed Drain Current (Note 8)				I _{DM}	18	A
Continuous Source Current (Body Diode) (Note 7)			Is	2.3	A	
Pulsed Source Current (Body Diode) (Note 8)			I _{SM}	18	A	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

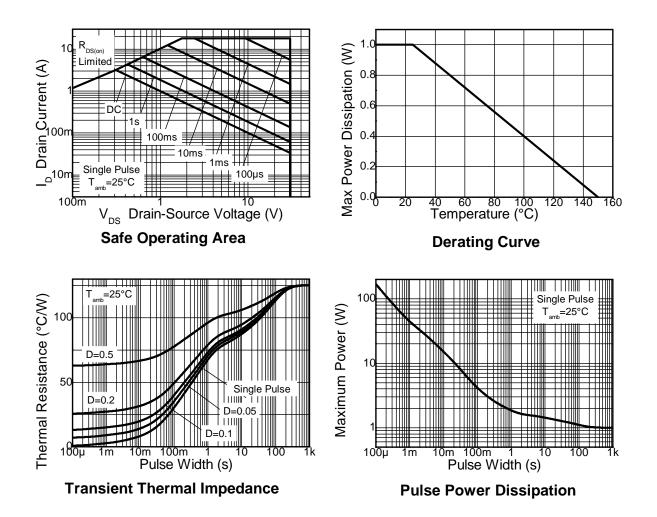
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P	1	W
Linear Derating Factor	PD	8	mW/°C
Power Dissipation (Note 7)	Р	1.5	W
Linear Derating Factor	PD	12	mW/°C
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	125	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	83	°C/W
Thermal Resistance, Junction to Leads (Note 9)	R _{θJL}	70.44	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

6. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
7. For a device surface mounted on FR4 PCB measured at t ≤5 secs.
8. Repetitive rating 25mm x 25mm FR4 PCB, D=0.02 pulse width=300µs - pulse current limited by maximum junction temperature.
9. Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

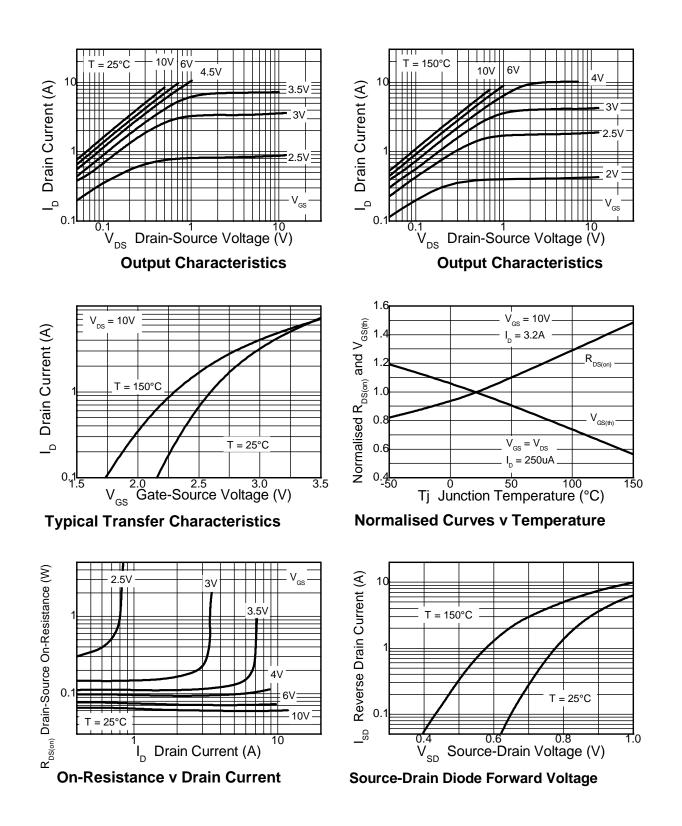
			-			T (0)
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS			1	1	r	
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	$I_{D} = 250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	I _{DSS}	_	—	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	1.0		2.2	V	$I_D = 250\mu A$, $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 10)			48	65	mΩ	$V_{GS} = 10V, I_D = 3.2A$
	R _{DS} (ON)	_	69	95	11152	$V_{GS} = 4.5V, I_D = 2.6A$
Forward Transconductance (Notes 10 and 12)	g fs	—	7.1	_	S	$V_{DS} = 15V, I_D = 3.2A$
Diode Forward Voltage (Note 10)	V _{SD}	—	0.85	0.95	V	$T_J = 25^{\circ}C$, $I_S = 2.5A$, $V_{GS} = 0V$
Reverse Recovery Time (Note 12)	t _{rr}	_	13	_	ns	T _J = 25°C, I _F = 1.6A, di/dt = 100A/µs
Reverse Recovery Charge (Note 12)	Qrr	_	7	_	nC	
DYNAMIC CHARACTERISTICS (Note 12)	•					-
Input Capacitance	Ciss	_	448	_		V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	Coss	_	82	_	pF	
Reverse Transfer Capacitance	C _{rss}	_	49	_		
Turn-On Delay Time (Note 11)	t _{D(on)}	_	2.4	_		
Turn-On Rise Time (Note 11)	tr	_	2.5	_		$\label{eq:VDD} \begin{array}{l} V_{DD} = 15V, \ I_D = 1A, \\ R_G \cong 6.0\Omega, \ V_{GS} = 10V \end{array}$
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	13.1	_	ns	
Turn-Off Fall Time (Note 11)	t _f	_	5.3	_		
Total Gate Charge (Note 11)	Qg	_	8.6			
Gate-Source Charge (Note 11)	Q _{gs}	_	1.4		nC	$V_{DS} = 15V, V_{GS} = 10V, I_D = 3.2A$
Gate-Drain Charge (Note 11)	Q _{gd}		1.8			

Notes:

Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.
 For design aid only, not subject to production testing.

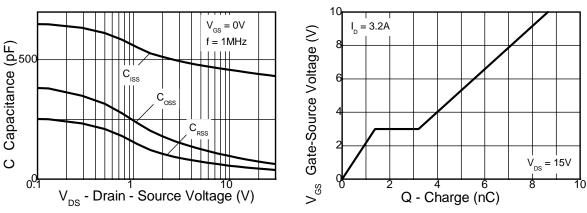


Typical Characteristics





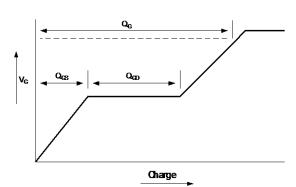
Typical Characteristics (continued)



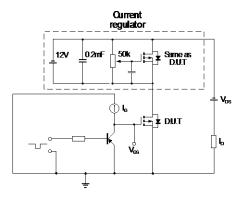
Capacitance v Drain-Source Voltage



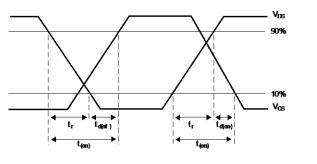
Test Circuits



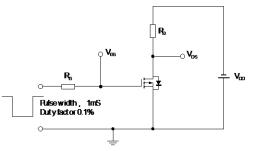
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

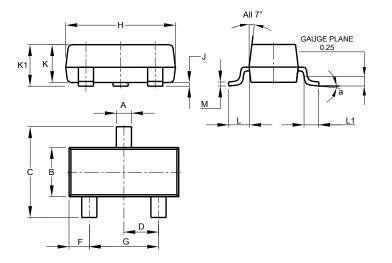


Switching time test circuit



Package Outline Dimensions

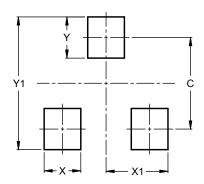
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
К	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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